

ZXMN2A02N8

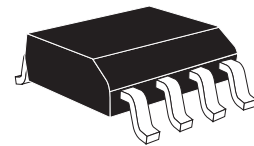
20V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 20V$; $R_{DS(ON)} = 0.02\Omega$; $I_D = 10.2A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



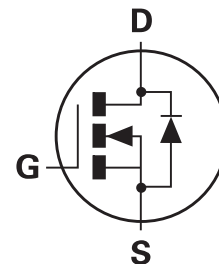
SO8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- Disconnect switches
- Motor control

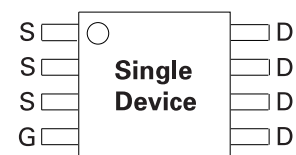


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN2A02N8TA	7"	12mm	500 units
ZXMN2A02N8TC	13"	12mm	2500 units

DEVICE MARKING

- ZXMN
2A02



Top View

ZXMN2A02N8

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	20	V
Gate Source Voltage	V_{GS}	± 12	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^\circ C$ ^(b) $V_{GS}=10V$; $T_A=70^\circ C$ ^(b) $V_{GS}=10V$; $T_A=25^\circ C$ ^(a)	I_D	10.2 8.2 8.3	A
Pulsed Drain Current ^(c)	I_{DM}	50	A
Continuous Source Current (Body Diode) ^(b)	I_S	4.3	A
Pulsed Source Current (Body Diode) ^(c)	I_{SM}	50	A
Power Dissipation at $T_A=25^\circ C$ ^(a) Linear Derating Factor	P_D	1.56 12.5	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ ^(b) Linear Derating Factor	P_D	2.5 20	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to 150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\theta JA}$	80	$^\circ C/W$
Junction to Ambient ^(b)	$R_{\theta JA}$	50	$^\circ C/W$

NOTES

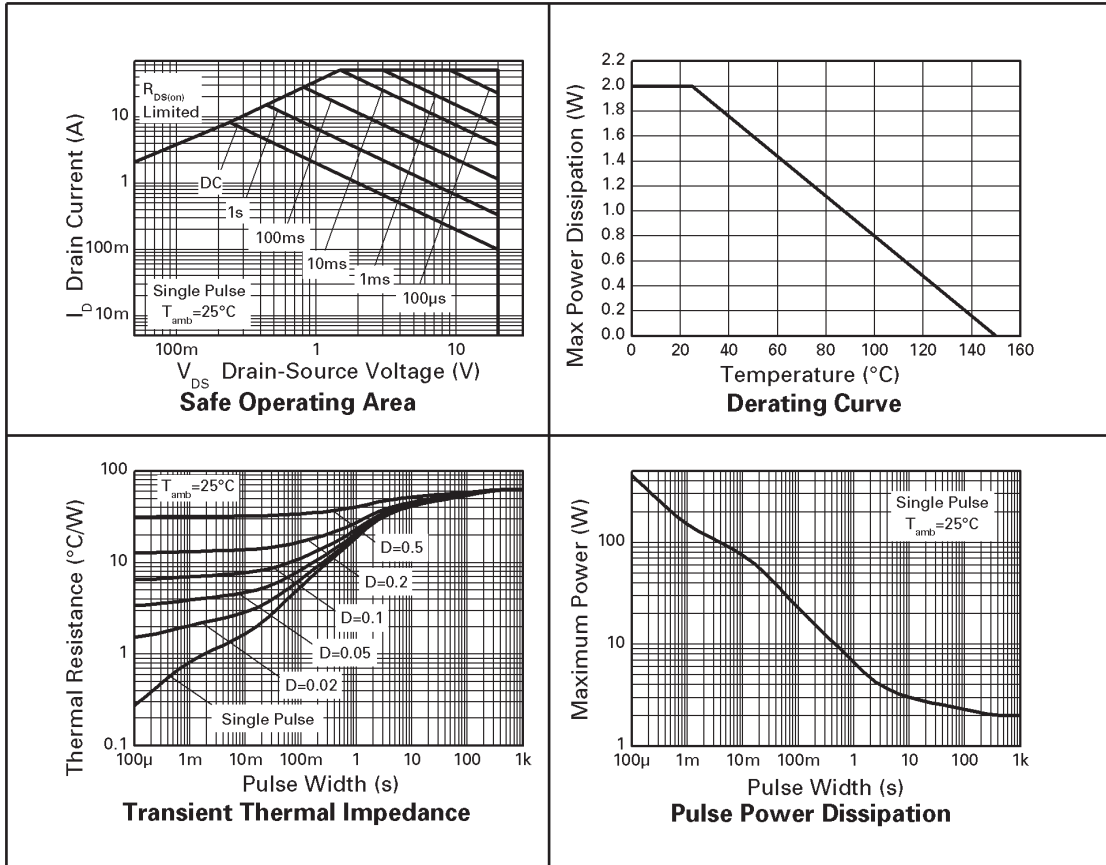
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

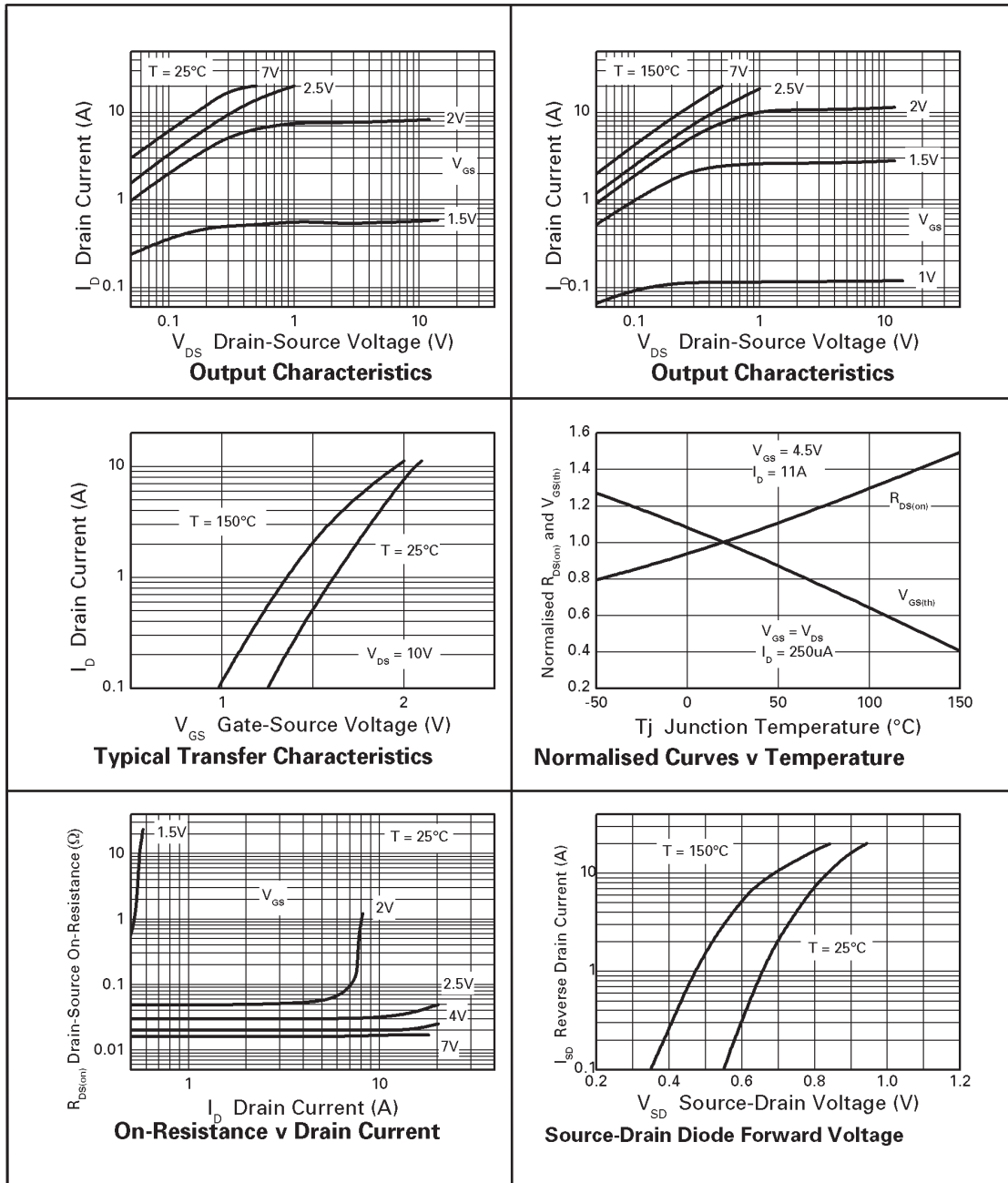
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V(BR)DSS	20			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =20V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =± 12V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	0.7			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance ⁽¹⁾	R _{DS(on)}			0.02	Ω	V _{GS} =4.5V, I _D =11A
				0.04	Ω	V _{GS} =2.5V, I _D =8.4A
Forward Transconductance ⁽¹⁾⁽³⁾	g _{fs}		27		S	V _{DS} =10V,I _D =11A
DYNAMIC ⁽³⁾						
Input Capacitance	C _{iss}		1900		pF	V _{DS} =10V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		356		pF	
Reverse Transfer Capacitance	C _{rss}		218		pF	
SWITCHING ^{(2) (3)}						
Turn-On Delay Time	t _{d(on)}		7.9		ns	V _{DD} =10V, I _D =1A R _G =6.0Ω, V _{GS} =4.5V
Rise Time	t _r		10		ns	
Turn-Off Delay Time	t _{d(off)}		33.3		ns	
Fall Time	t _f		13.6		ns	
Total Gate Charge	Q _g		18.9		nC	V _{DS} =10V,V _{GS} =4.5V, I _D =11A
Gate-Source Charge	Q _{gs}		5.2		nC	
Gate-Drain Charge	Q _{gd}		4.9		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage ⁽¹⁾	V _{SD}		0.85	0.95	V	T _J =25°C, I _S =11.5A, V _{GS} =0V
Reverse Recovery Time ⁽³⁾	t _{rr}		16.3		ns	T _J =25°C, I _F =2.1A,
Reverse Recovery Charge ⁽³⁾	Q _{rr}		7.8		nC	di/dt= 100A/μs

NOTES

- (1) Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

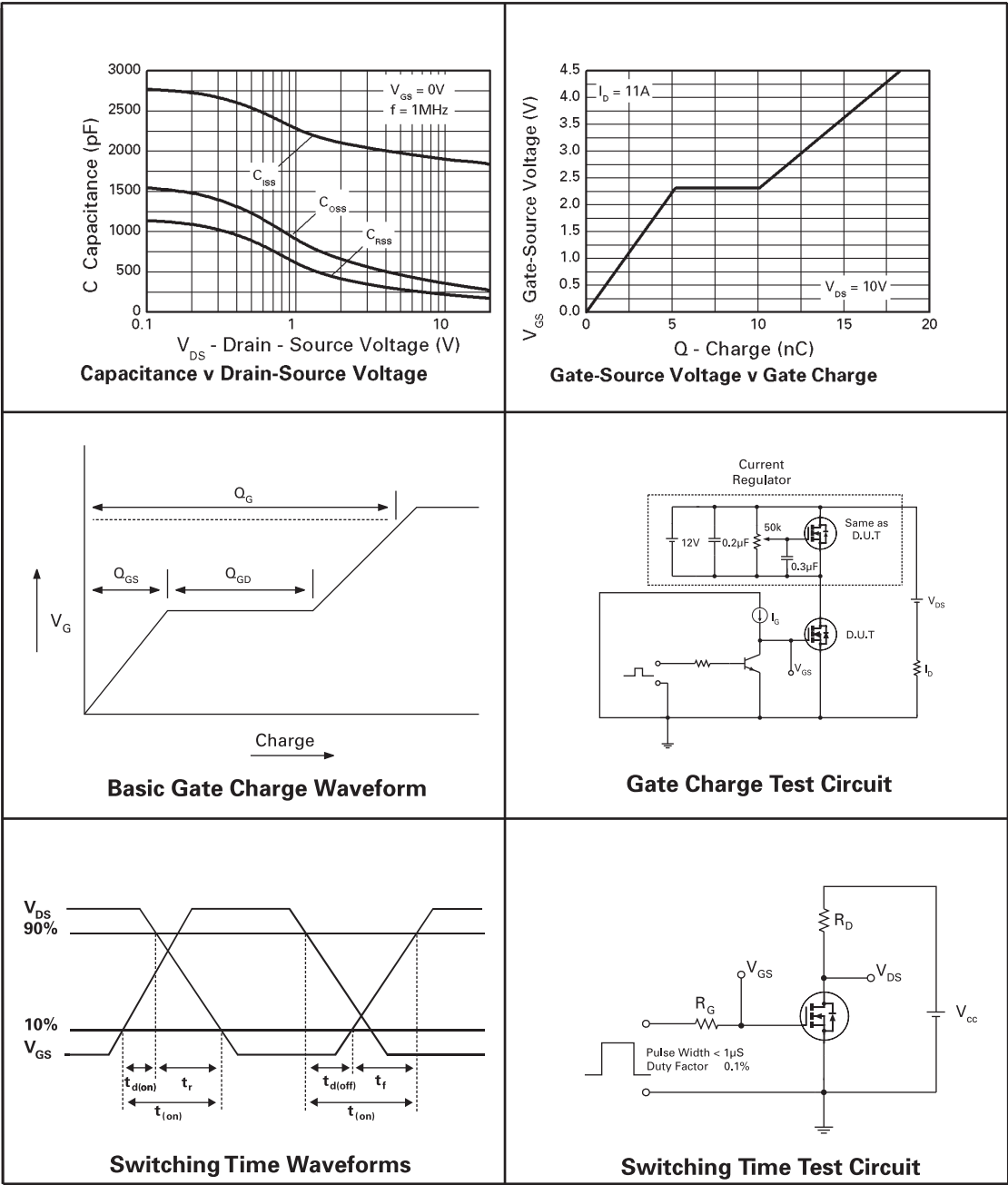
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CHARACTERISTICS



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"Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect

"Not recommended for new designs"Device is still in production to support existing designs and production

"Obsolete"Production has been discontinued

Datasheet status key:

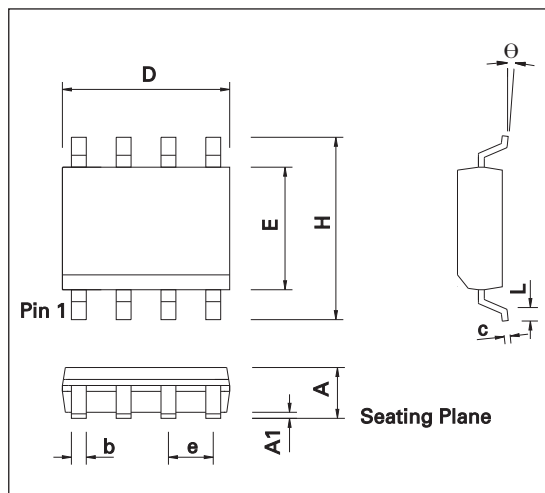
"Draft version" This term denotes a very early datasheet version and contains highly provisional information, which may change in any manner without notice.

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PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES
APPROX IN MILLIMETERS

PACKAGE DIMENSIONS

DIM	INCHES		MILLIMETRES	
	MIN	MAX	MIN	MAX
A	0.053	0.069	1.35	1.75
A1	0.004	0.010	0.10	0.25
D	0.189	0.197	4.80	5.00
H	0.228	0.244	5.80	6.20
E	0.150	0.157	3.80	4.00
L	0.016	0.050	0.40	1.27
e	0.050 BSC		1.27 BSC	
b	0.013	0.020	0.33	0.51
c	0.008	0.010	0.19	0.25
Θ	0°	8°	0°	8°
h	0.010	0.020	0.25	0.50

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